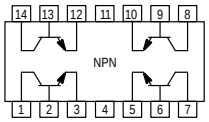
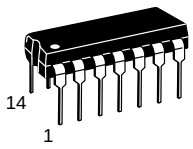
Quad Amplifier Transistors

NPN Silicon



MPQ2483
MPQ2484*

***Motorola Preferred Device**



CASE 646–06, STYLE 1
TO–116

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector–Emitter Voltage	V_{CEO}	40		Vdc
Collector–Base Voltage	V_{CBO}	60		Vdc
Emitter–Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	50		mAdc
		Each Transistor	**Four Transistors Equal Power**	
Total Device Dissipation @ T_A = 25°C(1) Derate above 25°C	P_D	500 4.0	900 7.2	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	0.825 6.7	2.4 19.2	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic		Junction to Case	Junction to Ambient	Unit
Thermal Resistance	Each Die Effective, 4 Die	151 52	250 134	°C/W °C/W
Coupling Factors	Q1–Q4 or Q2–Q3 Q1–Q2 or Q3–Q4	34 2.0	70 26	% %

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage(2) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	—	—	Vdc
Collector–Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	60	—	—	Vdc
Emitter–Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	6.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 45 Vdc, I_E = 0)	I_{CBO}	—	—	20	nAdc
Emitter Cutoff Current (V_{EB} = 3.0 Vdc, I_C = 0)	I_{EBO}	—	—	20	nAdc

1. Second Breakdown occurs at power levels greater than 3 times the power dissipation rating.
2. Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2.0%.

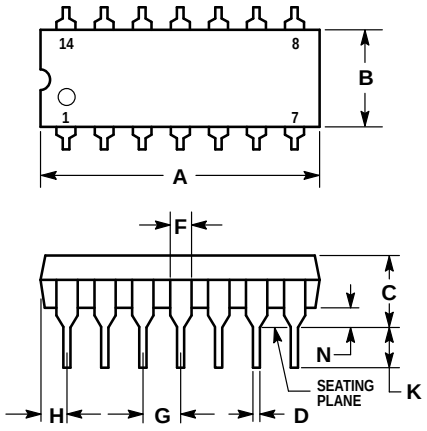
Preferred devices are Motorola recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS						
DC Current Gain(2)		h_{FE}				—
(I_C = 0.1 mAdc, V_{CE} = 5.0 Vdc)	MPQ2483		100	—	—	
	MPQ2484		200	—	—	
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	MPQ2483		150	—	—	
	MPQ2484		300	—	—	
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	MPQ2483		150	—	—	
	MPQ2484		300	—	—	
Collector–Emitter Saturation Voltage		$V_{CE(sat)}$				Vdc
(I_C = 1.0 mAdc, I_B = 0.1 mAdc)			—	0.13	0.35	
(I_C = 10 mAdc, I_B = 1.0 mAdc)			—	0.15	0.5	
Base–Emitter Saturation Voltage(2)		$V_{BE(sat)}$				Vdc
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc)			—	0.58	0.7	
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)			—	0.70	0.8	
SMALL–SIGNAL CHARACTERISTICS						
Current–Gain — Bandwidth Product (I_C = 500 μAdc, V_{CE} = 5.0 Vdc, f = 20 MHz)		f_T	50	100	—	MHz
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	4.0	8.0	pF
Collector–Base Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)		C_{cb}	—	1.8	6.0	pF
Noise Figure		NF				dB
(I_C = 10 μAdc, V_{CE} = 5.0 Vdc, R_S = 10 k ohms,	MPQ2483		—	3.0	—	
f = 1.0 kHz, BW = 10 kHz)	MPQ2484		—	2.0	—	

2. Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2.0%.

PACKAGE DIMENSIONS



STYLE 1:
PIN 1. COLLECTOR
2. BASE
3. EMITTER
4. NO CONNECTION
5. EMITTER
6. BASE
7. COLLECTOR
8. COLLECTOR
9. BASE
10. EMITTER
11. NO CONNECTION
12. EMITTER
13. BASE
14. COLLECTOR

NOTES:
1. LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE POSITION AT SEATING PLANE AT MAXIMUM MATERIAL CONDITION.
2. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
3. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
4. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.715	0.770	18.16	19.56
B	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
H	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.300 BSC		7.62 BSC	
M	0°	10°	0°	10°
N	0.015	0.039	0.39	1.01

CASE 646–06
TO–116
ISSUE M

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